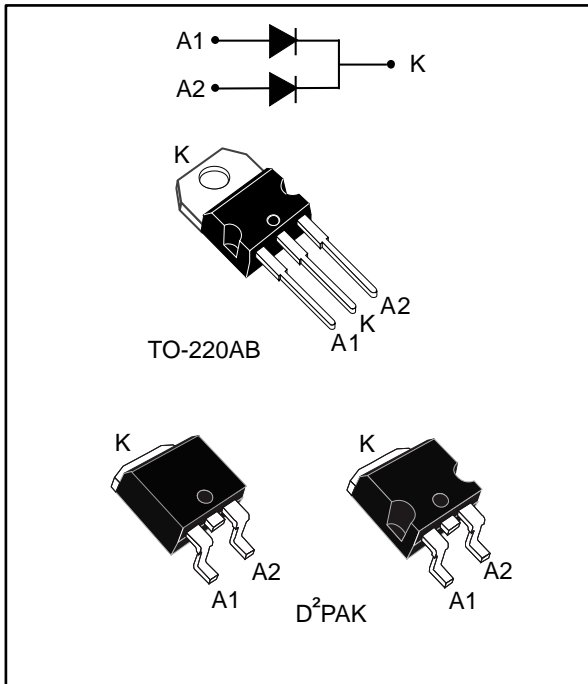


## Ultrafast recovery diode

Datasheet - production data



### Description

This series uses ST's new 400 V planar Pt doping technology. This device is specially suited for switching mode base drive and transistor circuits.

Packaged in through-the-hole and surface mount packages, this device is intended for use in low voltage, high frequency inverters, freewheeling and polarity protection.

Table 1: Device summary

Symbol	Value
$I_{F(AV)}$	2 x 8 A
$V_{RRM}$	400 V
$T_j$ (max)	175 °C
$V_F$ (typ)	0.9 V
$t_{rr}$ (typ)	25 ns

### Features

- Very low switching losses
- High frequency and/or high pulsed current operation
- High junction temperature
- ECOPACK®2 compliant component for D²PAK on demand

# 1 Characteristics

**Table 2: Absolute ratings (limiting values, per diode, at 25 °C, unless otherwise specified)**

Symbol	Parameter			Value	Unit
V <sub>RRM</sub>	Repetitive peak reverse voltage			400	V
I <sub>F(RMS)</sub>	Forward rms current			30	A
I <sub>F(AV)</sub>	Average forward current δ = 0.5, square wave	T <sub>C</sub> = 150 °C	Per diode	8	A
		T <sub>C</sub> = 145 °C	Per device	16	
I <sub>FSM</sub>	Surge non repetitive forward current	t <sub>p</sub> = 10 ms sinusoidal		120	A
T <sub>stg</sub>	Storage temperature range			-65 to +175	°C
T <sub>j</sub>	Maximum operating junction temperature range			-40 to +175	°C

**Table 3: Thermal parameter**

Symbol	Parameter		Max. value	Unit
R <sub>th(j-c)</sub>	Junction to case	Per diode	2	°C/W
		Per device	1.15	
R <sub>th(c)</sub>	Coupling		0.3	°C/W

When the diodes 1 and 2 are used simultaneously:

$$\Delta T_{j(\text{diode}1)} = P_{(\text{diode}1)} \times R_{th(j-c)} \text{ (per diode)} + P_{(\text{diode}2)} \times R_{th(c)}$$

**Table 4: Static electrical characteristics (per diode)**

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
I <sub>R</sub> <sup>(1)</sup>	Reverse leakage current	T <sub>j</sub> = 25 °C	V <sub>R</sub> = V <sub>RRM</sub>	-		10	µA
		T <sub>j</sub> = 125 °C		-	10	100	
V <sub>F</sub> <sup>(2)</sup>	Forward voltage drop	T <sub>j</sub> = 25 °C	I <sub>F</sub> = 8 A	-		1.5	V
		T <sub>j</sub> = 100 °C		-	1.05	1.3	
		T <sub>j</sub> = 150 °C		-	0.9	1.1	
		T <sub>j</sub> = 25 °C	I <sub>F</sub> = 16 A	-		1.75	
		T <sub>j</sub> = 100 °C		-	1.25	1.55	
		T <sub>j</sub> = 150 °C		-	1.12	1.37	

**Notes:**

<sup>(1)</sup>Pulse test: t<sub>p</sub> = 5 ms, δ < 2%

<sup>(2)</sup>Pulse test: t<sub>p</sub> = 380 µs, δ < 2%

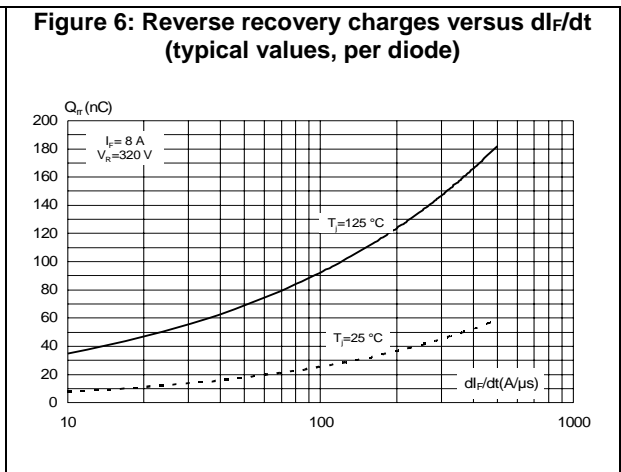
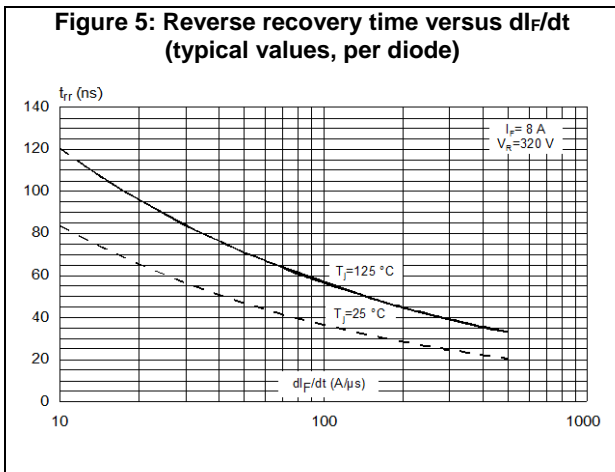
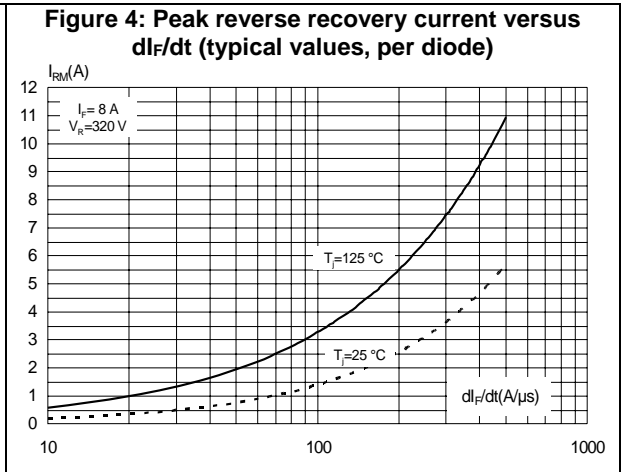
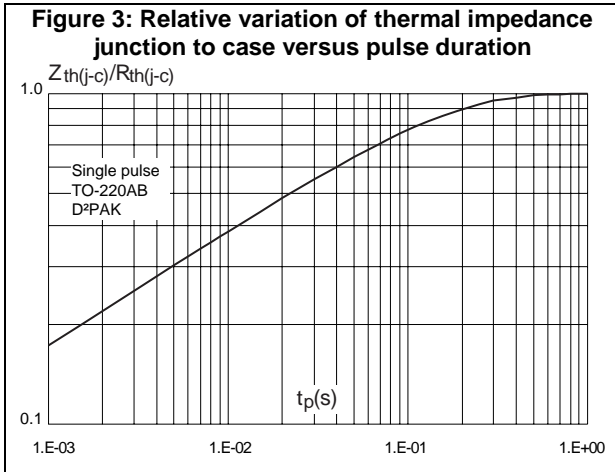
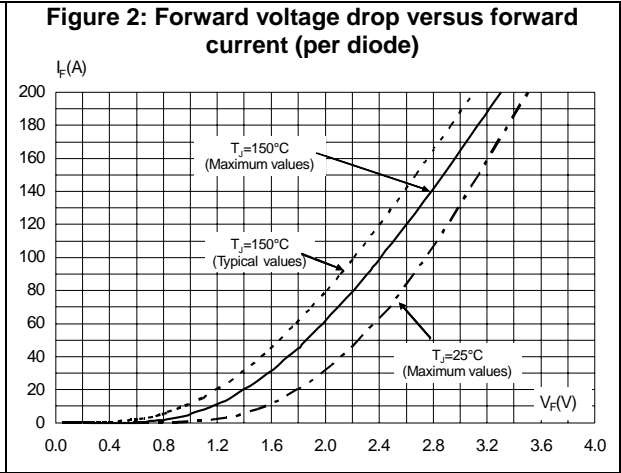
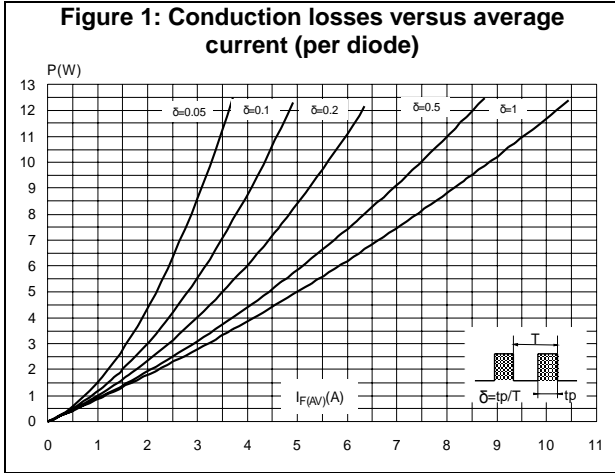
To evaluate the conduction losses, use the following equation:

$$P = 0.83 \times I_{F(AV)} + 0.034 \times I_{F(RMS)}^2$$

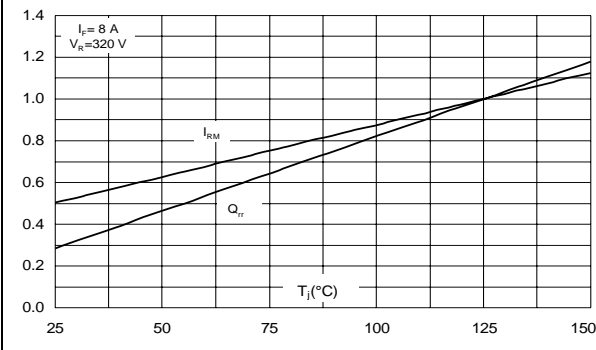
Table 5: Dynamic electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
t <sub>rr</sub>	Reverse recovery time	T <sub>j</sub> = 25 °C	I <sub>F</sub> = 1 A V <sub>R</sub> = 30 V di <sub>F</sub> /dt = -50 A/μs	-	35	50	ns
			I <sub>F</sub> = 1 A V <sub>R</sub> = 30 V di <sub>F</sub> /dt = -100 A/μs	-	25	35	
I <sub>RM</sub>	Reverse recovery current	T <sub>j</sub> = 125 °C	I <sub>F</sub> = 8 A V <sub>R</sub> = 320 V di <sub>F</sub> /dt = -200 A/μs	-	5.5	8	A
S <sub>factor</sub>	Softness factor			-	0.4	-	-
t <sub>fr</sub>	Forward recovery time	T <sub>j</sub> = 25 °C	I <sub>F</sub> = 8 A V <sub>FR</sub> = 1.1 x V <sub>F(max)</sub> di <sub>F</sub> /dt = 100 A/μs	-		150	ns
V <sub>FP</sub>	Forward recovery voltage			I <sub>F</sub> = 8 A di <sub>F</sub> /dt = 100 A/μs	-	2.9	

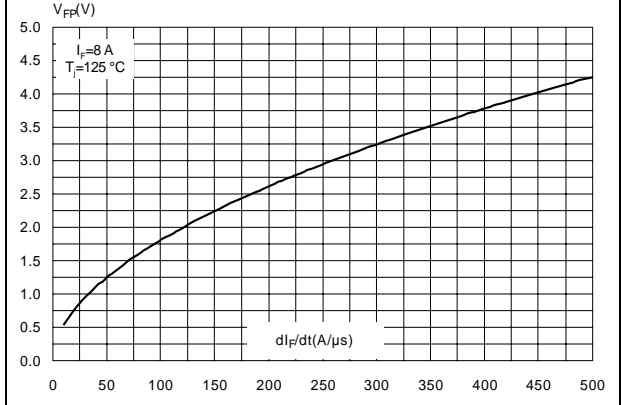
# 1.1 Characteristics (curves)



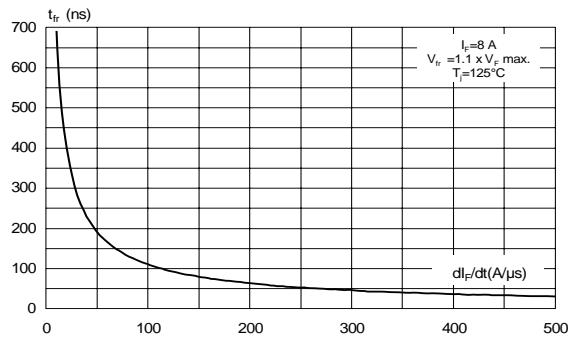
**Figure 7: Relative variations of dynamic parameters versus junction temperature (reference:  $T_j = 125^\circ\text{C}$ )**



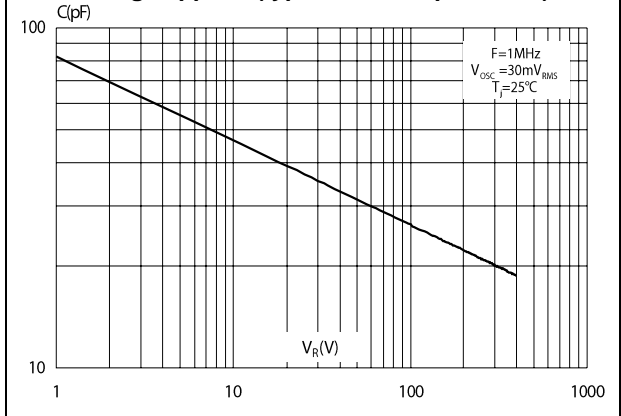
**Figure 8: Transient peak forward voltage versus  $di_F/dt$  (typical values, per diode)**



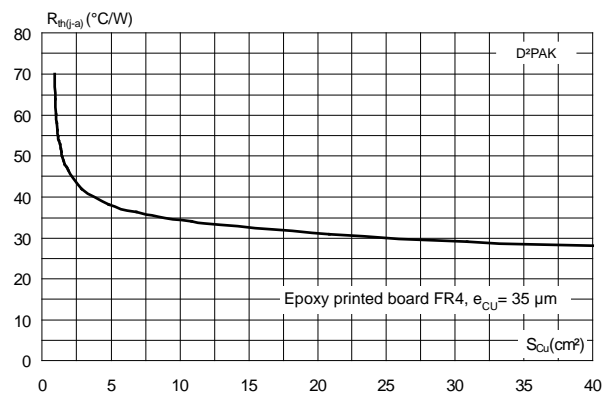
**Figure 9: Forward recovery time versus  $di_F/dt$  (typical values, per diode)**



**Figure 10: Junction capacitance versus reverse voltage applied (typical values, per diode)**



**Figure 11: Thermal resistance junction to ambient versus copper surface under tab**



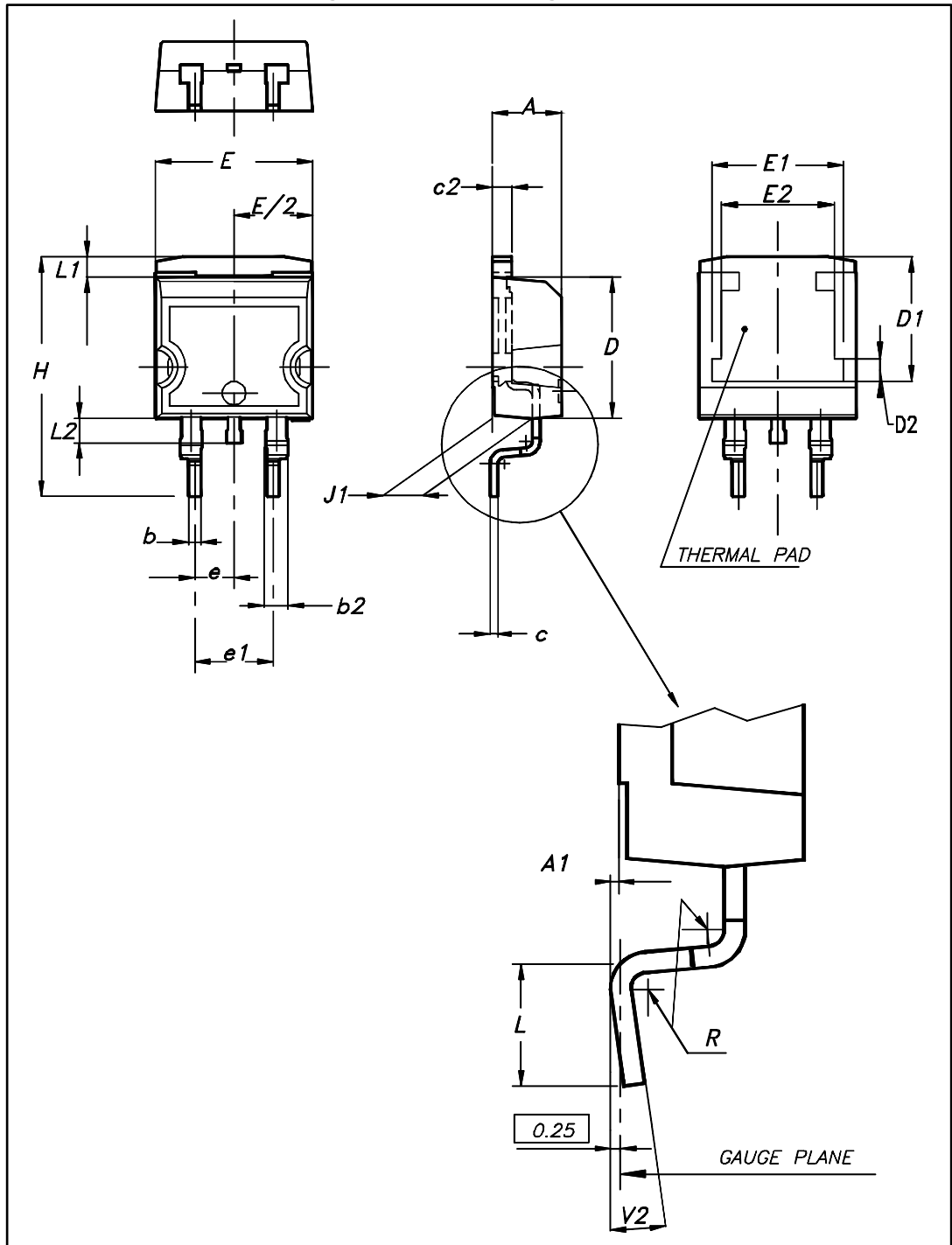
## 2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

- Cooling method: by conduction (C)
- Epoxy meets UL 94, V0
- Recommended torque value: 0.55 N·m (for TO-220AB)
- Maximum torque value: 0.7 N·m (for TO-220AB)

## 2.1 D<sup>2</sup>PAK package information

Figure 12: D<sup>2</sup>PAK package outline

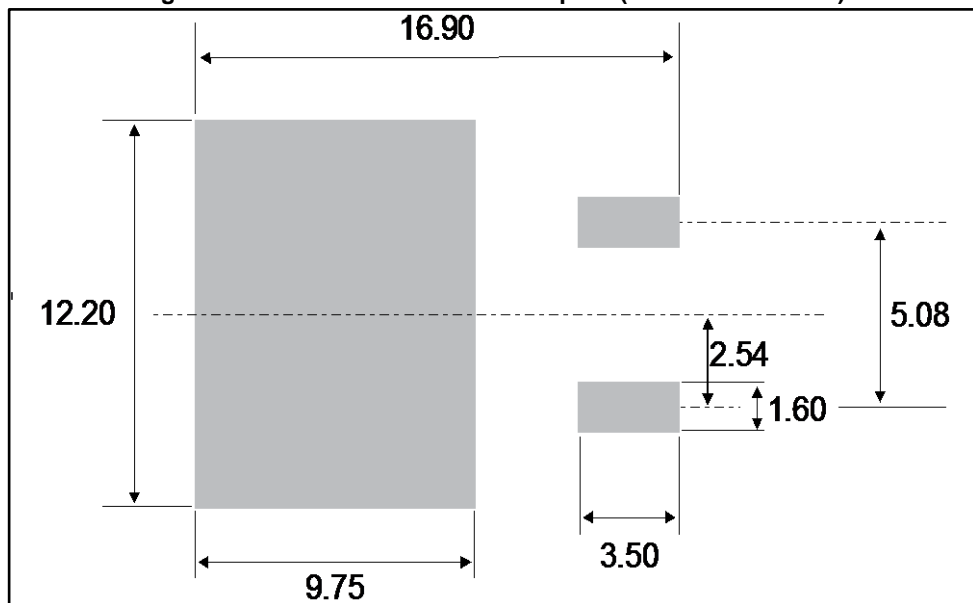


This package drawing may slightly differ from the physical package. However, all the specified dimensions are guaranteed.

Table 6: D<sup>2</sup>PAK package mechanical data

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.36	4.60	0.172	0.181
A1	0.00	0.25	0.000	0.010
b	0.70	0.93	0.028	0.037
b2	1.14	1.70	0.045	0.067
c	0.38	0.69	0.015	0.027
c2	1.19	1.36	0.047	0.053
D	8.60	9.35	0.339	0.368
D1	6.90	8.00	0.272	0.311
D2	1.10	1.50	0.043	0.060
E	10.00	10.55	0.394	0.415
E1	8.10	8.90	0.319	0.346
E2	6.85	7.25	0.266	0.282
e	2.54 typ.		0.100	
e1	4.88	5.28	0.190	0.205
H	15.00	15.85	0.591	0.624
J1	2.49	2.90	0.097	0.112
L	1.90	2.79	0.075	0.110
L1	1.27	1.65	0.049	0.065
L2	1.30	1.78	0.050	0.070
R	0.4 typ.		0.015	
V2	0°	8°	0°	8°

Figure 13: D<sup>2</sup>PAK recommended footprint (dimensions in mm)





## 2.2 TO-220AB package information

Figure 14: TO-220AB package outline

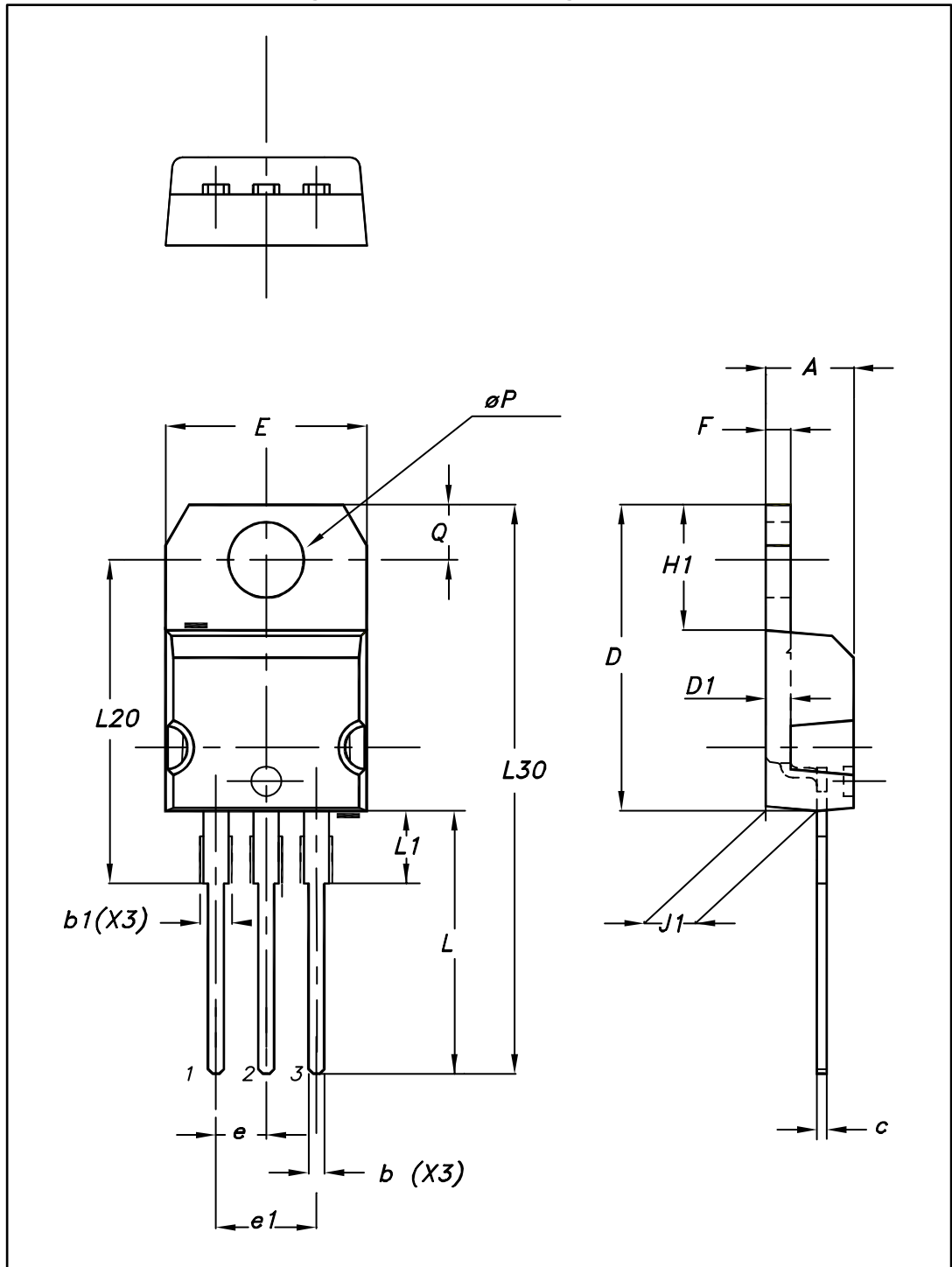


Table 7: TO-220AB package mechanical data

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
b	0.61	0.88	0.240	0.035
b1	1.14	1.70	0.045	0.067
c	0.48	0.70	0.019	0.028
D	15.25	15.75	0.600	0.620
D1	1.27 typ.		0.050 typ.	
E	10.00	10.40	0.394	0.409
e	2.40	2.70	0.094	0.106
e1	4.95	5.15	0.195	0.203
F	1.23	1.32	0.048	0.052
H1	6.20	6.60	0.244	0.260
J1	2.40	2.72	0.094	0.107
L	13.00	14.00	0.512	0.551
L1	3.50	3.93	0.138	0.155
L20	16.40 typ.		0.646 typ.	
L30	28.90 typ.		1.138 typ.	
θP	3.75	3.85	0.148	0.152
Q	2.65	2.95	0.104	0.116

### 3 Ordering information

Table 8: Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STTH16R04CT	STTH16R04CT	TO-220AB	1.9 g	50	Tube
STTH16R04CG-TR	STTH16R04CG	D <sup>2</sup> PAK	1.38 g	1000	Tape and reel

### 4 Revision history

Table 9: Document revision history

Date	Revision	Changes
31-Mar-2007	1	First issue.
02-Nov-2016	2	Removed device in TO-220FPAB. Updated features, <a href="#">Table 1: "Device summary"</a> and package silhouettes in cover page. Updated <a href="#">Section 1: "Characteristics"</a> , and <a href="#">Section 3: "Ordering information"</a> . Updated <a href="#">Section 2.1: "D<sup>2</sup>PAK package information"</a> .

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